WHAT IS CLAIMED IS:

1. A semiconductor device comprising:

a semiconductor element bonded on a first metallic layer;

a wire for electrically connecting an electrode pad of the semiconductor element to a second metallic layer; and

a resin package for sealing said semiconductor element,

wherein rear surfaces of the first metallic layer and the second metallic layer are flush with a bottom of said resin package.

2. A semiconductor device according to claim 1, wherein the first metallic layer has a larger area than that of a bottom surface of the semiconductor element.

3. A semiconductor device according to claim 1, wherein said first metallic layer is thicker than said second metallic layer, and said first metallic layer has a smaller area than a bottom area of the semiconductor element.

4. A semiconductor device according to claim 1, wherein said second metallic layer is individually exposed from a bottom of said resin package.

5. A method of manufacturing a semiconductor device comprising the steps of:

forming an electrodeposition frame on a flexible flat metallic substrate, said electrodeposition frame with first metallic layers and second metallic layers for external extension being patterned;

contiguously mounting a plurality of semiconductor elements each with electrode pads thereon, on said first metallic layers, respectively;

wire-bonding the electrode pads to said second metallic layers which are located between said semiconductor elements;

resin-sealing said semiconductor elements mounted on said electrodeposition frame;

removing said metallic substrate to provide a resin sealing body; and

cutting said resin sealing body into individual semiconductor devices with the air of cutting marks formed the first and second metallic layers.

6. A method of manufacturing a semiconductor device according to claim 5, further comprising after the step of cutting, the step of:

depositing metallic layers for electrodes to the second metallic layers exposed from a rear surface of said resin sealing body.

7. A method of manufacturing a semiconductor device according to claim 5, wherein

in said step of cutting of said resin sealing body, it is cut along a center line of each of the second metallic layers to provide metallic layers for external extension for adjacent semiconductor elements.

8. A method of manufacturing a semiconductor device

according to claim 5, wherein said electrodeposition frame is resin sealed together with said semiconductor elements using said metallic substrate as a lower die.